CLAIMS:

1. A method of forming a polished material, comprising:

providing a substrate;

forming a trench within the substrate and an etchstop proximate the trench, the substrate having a surface and the etchstop having an uppermost surface above the substrate surface;

forming a material within the trench and extending to above the etchstop uppermost surface, the material comprising a lower layer and an upper layer, the lower layer polishing at slower rate than the upper layer under common polishing conditions, the lower layer joining the upper layer at an interface; and

polishing the material down to at or below about an elevational level of the etchstop uppermost surface utilizing the common polishing conditions.

2. The method of claim 1 wherein the interface extends to below an elevational level of the etchstop uppermost surface.

3. The method of claim 1 wherein a lowermost portion of the interface is above an elevational level of the etchstop uppermost surface.

4. The method of claim 1 wherein the interface extends to a location below an elevational level of the etchstop uppermost surface and at least as high as about an elevational level of the substrate surface.

5. The method of claim 1 wherein the upper and lower layers comprise silicon dioxide.

6. The method of claim 1 wherein the trench comprises a substantially vertical sidewall.

7. The method of claim 1 wherein the substrate comprises monocrystalline silicon, and wherein the etchstop comprises silicon nitride.

8. The method of claim 1 wherein the material formed within the trench comprises silicon dioxide, and wherein the lower layer of the silicon dioxide comprises a higher density than the upper layer of the silicon dioxide.

9. A method of forming a polished material, comprising:

providing a substrate and providing an elevational step relative to the substrate, the elevational step having an uppermost surface;

forming a material beside the elevational step and extending to above the elevational step uppermost surface, the material comprising a lower layer and an upper layer, the lower layer polishing at slower rate than the upper layer under common polishing conditions, the lower layer joining the upper layer at an interface; and

polishing the material down to about the elevational level of the elevational step uppermost surface utilizing the common polishing conditions.

10. The method of claim 9 wherein the interface extends to at or below an elevational level of the elevational step uppermost surface.

11. The method of claim 9 wherein the upper and lower layers comprise silicon dioxide.

12. The method of claim 9 wherein the step comprises a substantially vertical sidewall.

13. The method of claim 9 wherein the material is formed to extend over the elevational step uppermost surface, and wherein the polishing removes the material from over the elevational step uppermost surface.

14. The method of claim 9 wherein the substrate comprises monocrystalline silicon, and wherein the elevational step comprises both monocrystalline silicon and silicon nitride.

15. The method of claim 9 wherein the substrate comprises monocrystalline silicon, wherein the elevational step comprises both monocrystalline silicon and silicon nitride, wherein the silicon nitride is a layer over the monocrystalline silicon and has an upper surface coextensive with the elevational step uppermost surface, the monocrystalline silicon having an upper surface, and the interface having a lowestmost portion at an elevational level between the elevational level of the elevational step uppermost surface and an elevational level of the monocrystalline silicon upper surface.

16. The method of claim 9 wherein the interface extends to below the elevational level of the elevational step uppermost surface.

17. The method of claim 9 wherein the upper and lower layers comprise silicon dioxide and are formed by plasma deposition; the lower layer being formed while maintaining a temperature of the substrate at from about 500°C to about 700°C, and the upper layer being formed while maintaining a temperature of the substrate at from about 300°C to about 400°C.

18. A method of forming a polished material, comprising:

providing a substrate and providing an elevational step relative to the substrate, the elevational step having an uppermost surface;

forming a material beside the elevational step and extending to above the elevational step uppermost surface, the material comprising a lower layer and an upper layer, the lower layer polishing at slower rate than the upper layer under common polishing conditions, the lower layer joining the upper layer at an interface; and

polishing the material at least down to the interface utilizing the common polishing conditions.

19. A method of forming a polished material, comprising:

providing a substrate and providing an elevational step relative to the substrate, the elevational step having an uppermost surface;

forming a material beside the elevational step and extending to above the elevational step uppermost surface, the material comprising a lower layer and an upper layer, the lower layer being more dense than the upper layer, the lower layer joining the upper layer at an interface that extends to at or below an elevational level of the elevational step uppermost surface; and

polishing the material at least down to about the elevational level of the elevational step uppermost surface.

20. The method of claim 19 wherein the polishing comprises chemical-mechanical polishing.

21. The method of claim 19 wherein the material is formed to extend over the elevational step uppermost surface, and wherein the polishing removes the material from over the elevational step uppermost surface.

22. The method of claim 19 wherein the upper and lower layers comprise silicon dioxide.

23. The method of claim 19 wherein the substrate comprises monocrystalline silicon, and wherein the elevational step comprises both monocrystalline silicon and silicon nitride.

24. The method of claim 19 wherein the interface extends to below the elevational level of the elevational step uppermost surface.

25. The method of claim 19 wherein the upper and lower layers comprise silicon dioxide and are formed by plasma deposition; the lower layer being formed while maintaining a temperature of the substrate at from about 500°C to about 700°C, and the upper layer being formed while maintaining a temperature of the substrate at from about 300°C to about 400°C.

26. A method of polishing a material, comprising:

providing a substrate having an opening extending therein, the substrate having a surface proximate the opening;

forming a material within the opening and extending to above the substrate surface, the material comprising a lower layer and an upper layer, one of the lower and upper layers polishing at a slower rate than the other of the lower and upper layers under common polishing conditions, the lower layer joining the upper layer at an interface that extends from above an elevational level of the substrate surface to below said elevational level; and

polishing the material at least at least down to about the elevational level of the substrate surface utilizing the common polishing conditions.

27. The method of claim 26 wherein the lower layer polishes at the slower rate.

28. A method of forming a trench isolation region, comprising:

providing a substrate having a trench opening extending therein, the substrate having a surface proximate the opening;

forming an insulative material within the opening and extending to above the substrate surface, the material comprising a lower layer and an upper layer, the lower layer polishing at a slower rate than the upper layer under common polishing conditions, the lower layer joining the upper layer at an interface that extends to at or below an elevational level of the substrate surface; and

polishing the material at least down to about the elevational level of the substrate surface utilizing the common polishing conditions.

29. The method of claim 28 wherein the upper and lower layers consist essentially of the same chemical composition and differ only in density.

30. The method of claim 28 wherein the upper and lower layers comprise silicon dioxide.

31. The method of claim 28 wherein the material is formed to extend over the substrate surface, and wherein the polishing removes the material from over the substrate surface.

32. The method of claim 28 wherein the interface extends to below the elevational level of the substrate surface.

33. The method of claim 28 wherein the substrate comprises a silicon nitride layer over monocrystalline silicon, wherein the opening extends through the silicon nitride layer and into the monocrystalline silicon, and wherein the substrate surface is a surface of the silicon nitride layer.

34. The method of claim 28 wherein the upper and lower layers comprise silicon dioxide and are formed by plasma deposition; the lower layer being formed while maintaining a temperature of the substrate at from about 500°C to about 700°C, and the upper layer being formed while maintaining a temperature of the substrate at from about 300°C to about 400°C.

35. A method of forming an isolation region, comprising:

providing a substrate having an opening extending therein, the substrate having a surface proximate the opening;

forming a material within the opening and extending to above the substrate surface, the material comprising a lower layer and an upper layer, one of the upper and lower layers being more dense than the other of the upper and lower layers, the lower layer joining the upper layer at an interface that extends from over an elevational level of the substrate surface to at or below said elevational level; and

polishing the material at least down to about the elevational level of the substrate surface.

36. The method of claim 35 wherein the lower layer is more dense than the upper layer.

37. A method of forming an isolation region, comprising:

providing a substrate having an opening extending therein, the substrate having a surface proximate the opening;

forming a material within the opening and extending to above the substrate surface, the material comprising a lower layer and an upper layer, the lower layer being more dense than the upper layer, the lower layer joining the upper layer at an interface that extends to at or below an elevational level of the substrate surface; and

polishing the material at least down to about the elevational level of the substrate surface.

38. The method of claim 37 wherein the upper and lower layers consist essentially of the same chemical composition and differ only in density.

39. The method of claim 37 wherein the upper and lower layers comprise silicon dioxide.

40. The method of claim 37 wherein the material is formed to extend over the substrate surface, and wherein the polishing removes the material from over the substrate surface.

41. The method of claim 37 wherein the interface extends to below the elevational level of the substrate surface.

42. The method of claim 37 wherein the substrate comprises a silicon nitride layer over monocrystalline silicon, wherein the opening extends through the silicon nitride layer and into the monocrystalline silicon, and wherein the substrate surface is a surface of the silicon nitride layer.

43. The method of claim 37 wherein the upper and lower layers comprise silicon dioxide and are formed by plasma deposition; the lower layer being formed while maintaining a temperature of the substrate at from about 500°C to about 700°C, and the upper layer being formed while maintaining a temperature of the substrate at from about 300°C to about 400°C.

44. A method of forming an isolation region, comprising:

providing a bulk monocrystalline silicon substrate;

forming a patterned layer over the substrate, the patterned layer defining an opening over the substrate and comprising an upper surface proximate the opening;

extending the opening into the substrate;

forming a material within the opening and extending to above the patterned layer upper surface, the material comprising a lower layer and an upper layer, the lower layer being more dense than the upper layer, the lower layer joining the upper layer at an interface that extends to at or below an elevational level of the upper surface; and

polishing the material at least down to about the elevational level of the upper surface.

45. The method of claim 44 wherein the patterned layer comprises silicon nitride, the silicon nitride of the patterned layer being separated from the monocrystalline silicon by a layer of silicon dioxide.

46. The method of claim 44 wherein the material is formed to extend over the patterned layer upper surface, and wherein the polishing removes the material from over the patterned layer upper surface.

47. The method of claim 44 wherein the upper and lower layers comprise silicon dioxide.

48. The method of claim 44 wherein the interface extends to below the elevational level of the patterned layer upper surface.

49. The method of claim 44 wherein the upper and lower layers comprise silicon dioxide and are formed by plasma deposition; the lower layer being formed while maintaining a temperature of the substrate at from about 500°C to about 700°C, and the upper layer being formed while maintaining a temperature of the substrate at from about 300°C to about 400°C.